

# EMG2DXV5, EMG5DXV5

## Dual Bias Resistor Transistors

### NPN Silicon Surface Mount Transistors with Monolithic Bias Resistor Network

This new series of digital transistors is designed to replace a single device and its external resistor bias network. The BRT (Bias Resistor Transistor) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space. The device is housed in the SOT-553 package which is designed for low power surface mount applications.

#### Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- Moisture Sensitivity Level: 1
- Available in 8 mm, 7 inch Tape and Reel
- Lead-Free Solder Plating
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Base Voltage	$V_{CB0}$	50	Vdc
Collector-Emitter Voltage	$V_{CEO}$	50	Vdc
Collector Current	$I_C$	100	mAdc

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	230 (Note 1) 338 (Note 2) 1.8 (Note 1) 2.7 (Note 2)	mW $^\circ\text{C/W}$
Thermal Resistance – Junction-to-Ambient	$R_{\theta JA}$	540 (Note 1) 370 (Note 2)	$^\circ\text{C/W}$
Thermal Resistance – Junction-to-Lead	$R_{\theta JL}$	264 (Note 1) 287 (Note 2)	$^\circ\text{C/W}$
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

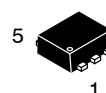
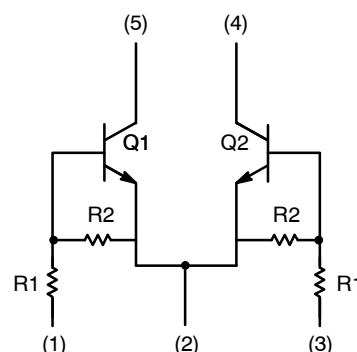
1. FR-4 @ Minimum Pad
2. FR-4 @ 1.0 x 1.0 inch Pad



ON Semiconductor®

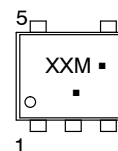
<http://onsemi.com>

### NPN SILICON BIAS RESISTOR TRANSISTORS



SOT-553  
CASE 463B

#### MARKING DIAGRAM



XX = UF (EMG5)  
UP (EMG2)  
M = Date Code  
■ = Pb-Free Package

(Note: Microdot may be in either location)

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

# EMG2DXV5, EMG5DXV5

## DEVICE MARKING AND RESISTOR VALUES

Device	Package	Marking	R1 (K)	R2 (K)
EMG2DXV5	SOT-553	UP	47	47
EMG5DXV5	SOT-553	UF	10	47

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
----------------	--------	-----	-----	-----	------

### OFF CHARACTERISTICS (Q1 & Q2)

Collector-Base Cutoff Current (V <sub>CB</sub> = 50 V, I <sub>E</sub> = 0)	I <sub>CBO</sub>	–	–	100	nAdc
Collector-Emitter Cutoff Current (V <sub>CE</sub> = 50 V, I <sub>B</sub> = 0)	I <sub>CEO</sub>	–	–	500	nAdc
Emitter-Base Cutoff Current (V <sub>EB</sub> = 6.0 V, I <sub>C</sub> = 0)	I <sub>EBO</sub>	–	–	0.1	mAdc
		–	–	0.2	
Collector-Base Breakdown Voltage (I <sub>C</sub> = 10 μA, I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	50	–	–	Vdc
Collector-Emitter Breakdown Voltage (Note 3) (I <sub>C</sub> = 2.0 mA, I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	50	–	–	Vdc

### ON CHARACTERISTICS (Q1 & Q2) (Note 3)

DC Current Gain (V <sub>CE</sub> = 10 V, I <sub>C</sub> = 5.0 mA)	EMG2DXV5 EMG5DXV5	h <sub>FE</sub>	80 80	140 140	– –	
Collector-Emitter Saturation Voltage (I <sub>C</sub> = 10 mA, I <sub>B</sub> = 0.3 mA)		V <sub>CE(sat)</sub>	–	–	0.25	Vdc
Output Voltage (on) (V <sub>CC</sub> = 5.0 V, V <sub>B</sub> = 3.5 V, R <sub>L</sub> = 1.0 kΩ)	EMG2DXV5	V <sub>OL</sub>	–	–	0.2	Vdc
(V <sub>CC</sub> = 5.0 V, V <sub>B</sub> = 2.5 V, R <sub>L</sub> = 1.0 kΩ)	EMG5DXV5		–	–	0.2	
Output Voltage (off) (V <sub>CC</sub> = 5.0 V, V <sub>B</sub> = 0.5 V, R <sub>L</sub> = 1.0 kΩ)		V <sub>OH</sub>	4.9	–	–	Vdc
Input Resistor	EMG2DXV5 EMG5DXV5	R <sub>1</sub>	32.9 7.0	47 10	61.1 13	kΩ
Resistor Ratio	EMG2DXV5 EMG5DXV5	R <sub>1</sub> /R <sub>2</sub>	0.8 0.17	1.0 0.21	1.2 0.25	

3. Pulse Test: Pulse Width < 300 μs, Duty Cycle < 2.0%

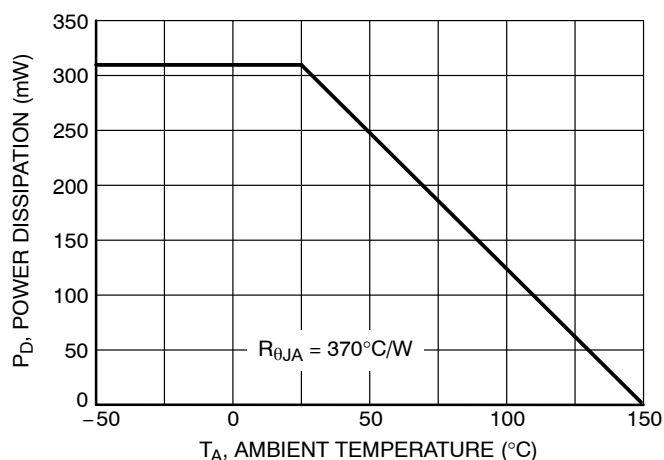


Figure 1. Derating Curve

# EMG2DXV5, EMG5DXV5

## TYPICAL ELECTRICAL CHARACTERISTICS — EMG2DXV5

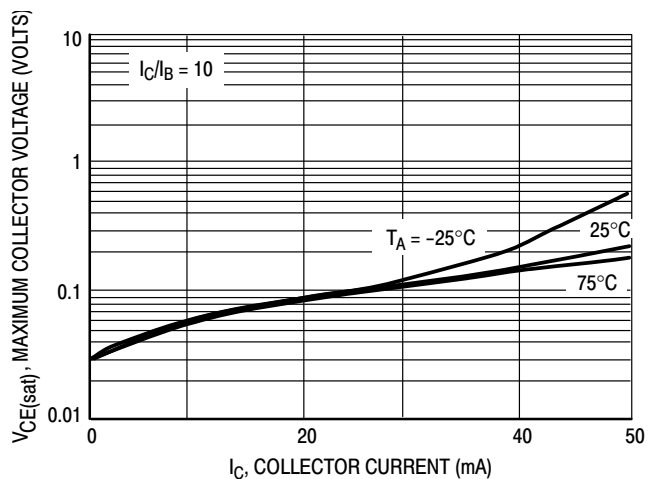


Figure 2.  $V_{CE(sat)}$  versus  $I_C$

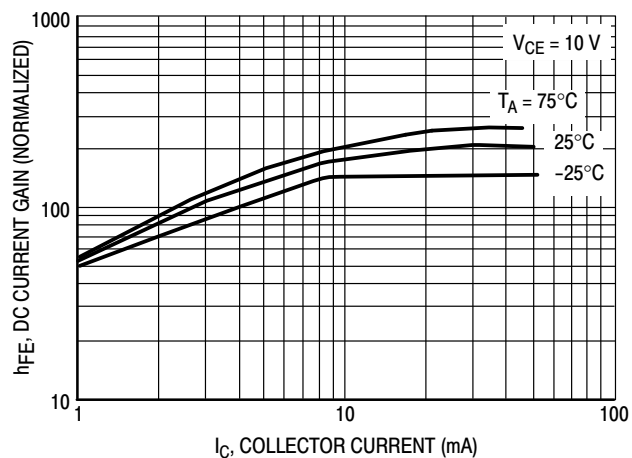


Figure 3. DC Current Gain

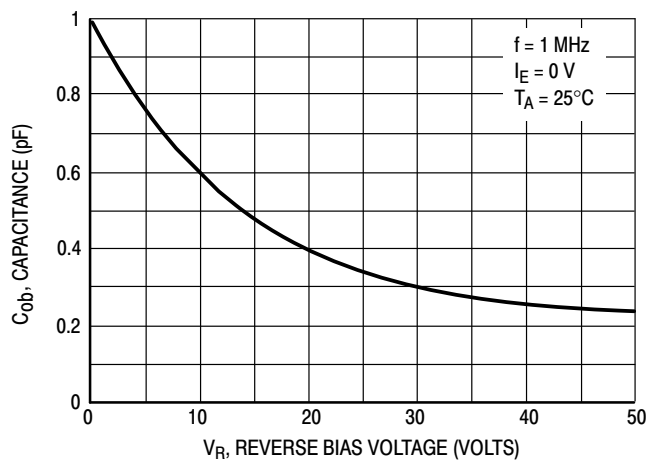


Figure 4. Output Capacitance

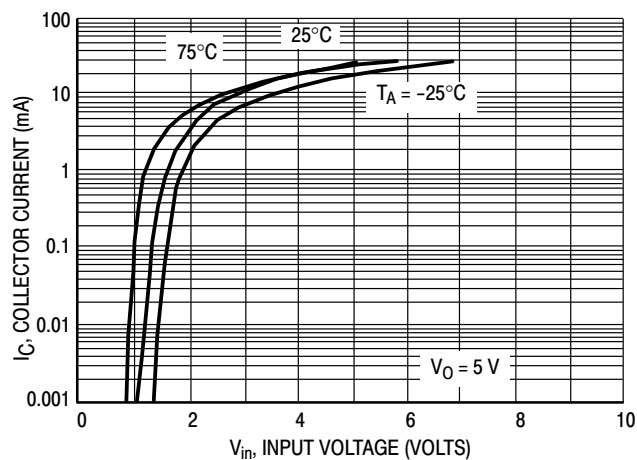


Figure 5. Output Current versus Input Voltage

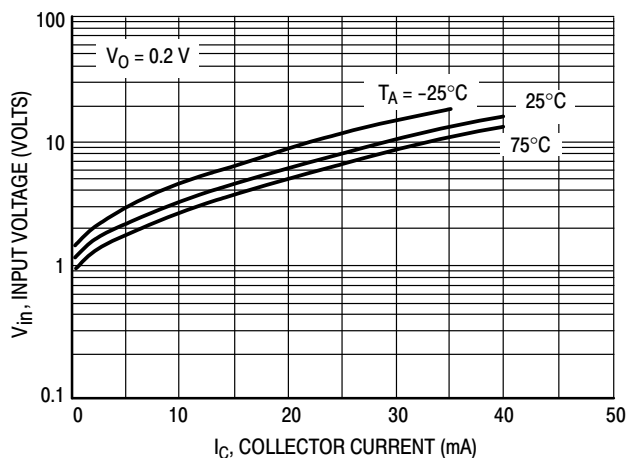


Figure 6. Input Voltage versus Output Current

# EMG2DXV5, EMG5DXV5

## TYPICAL ELECTRICAL CHARACTERISTICS – EMG5DXV5

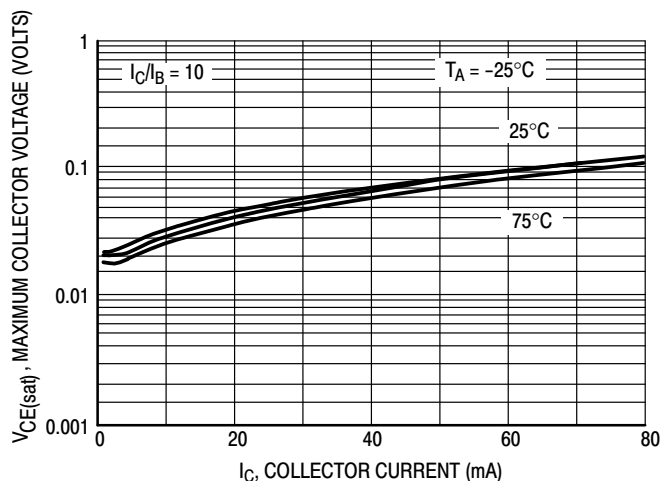


Figure 7.  $V_{CE(sat)}$  versus  $I_C$

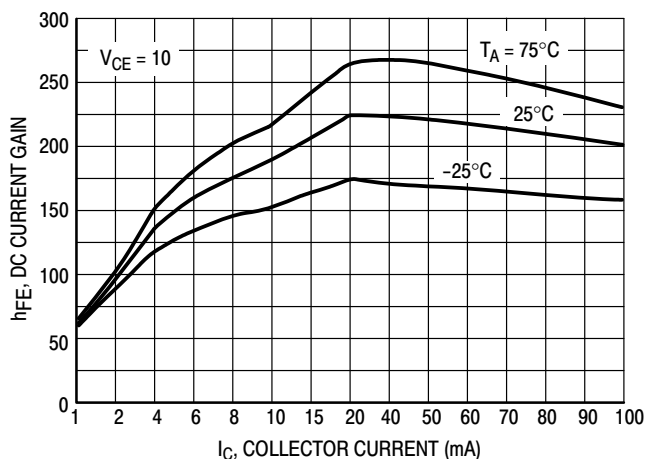


Figure 8. DC Current Gain

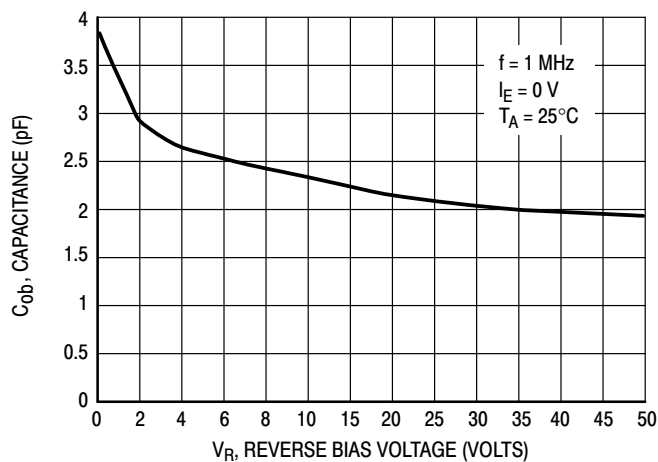


Figure 9. Output Capacitance

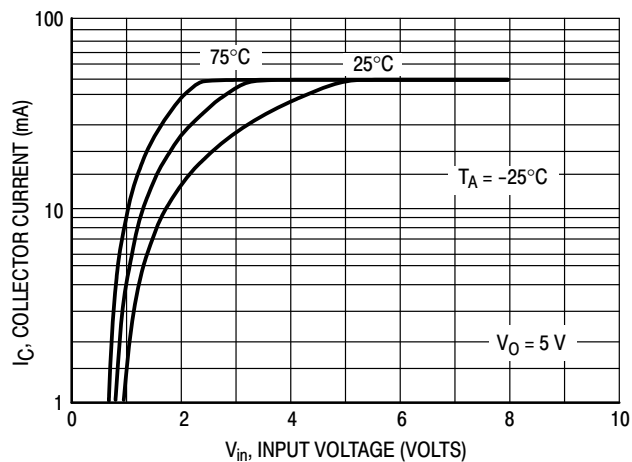


Figure 10. Output Current versus Input Voltage

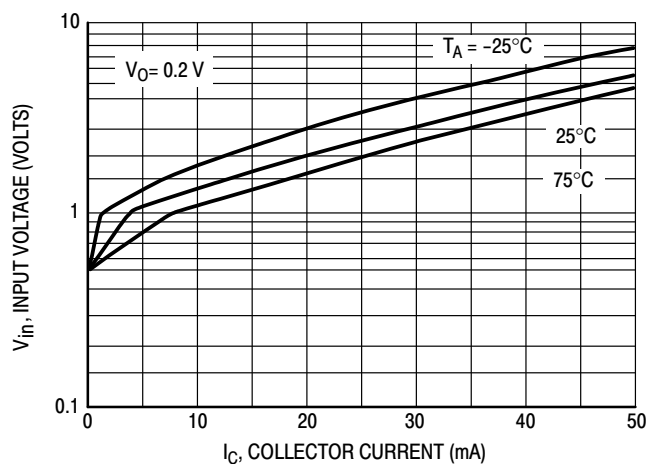


Figure 11. Input Voltage versus Output Current

## EMG2DXV5, EMG5DXV5

### TYPICAL APPLICATIONS FOR NPN BRTs

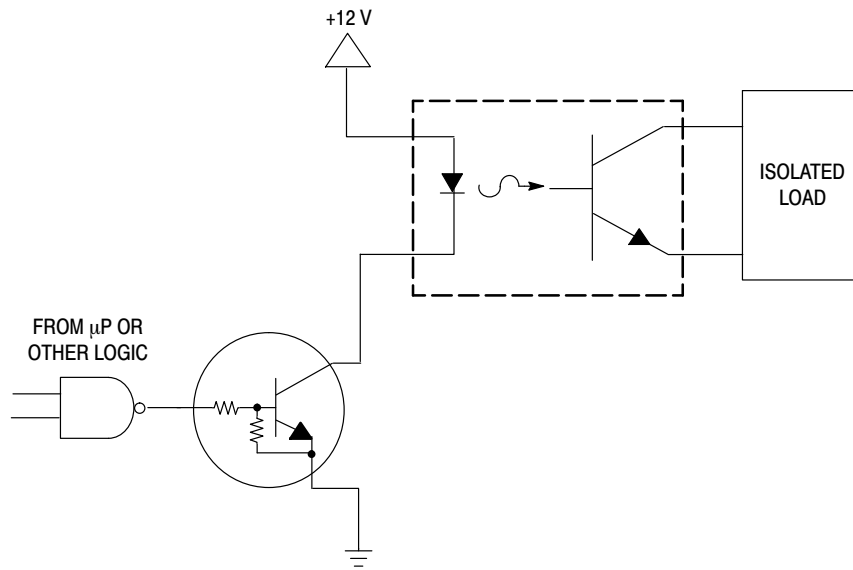


Figure 12. Level Shifter: Connects 12 or 24 Volt Circuits to Logic

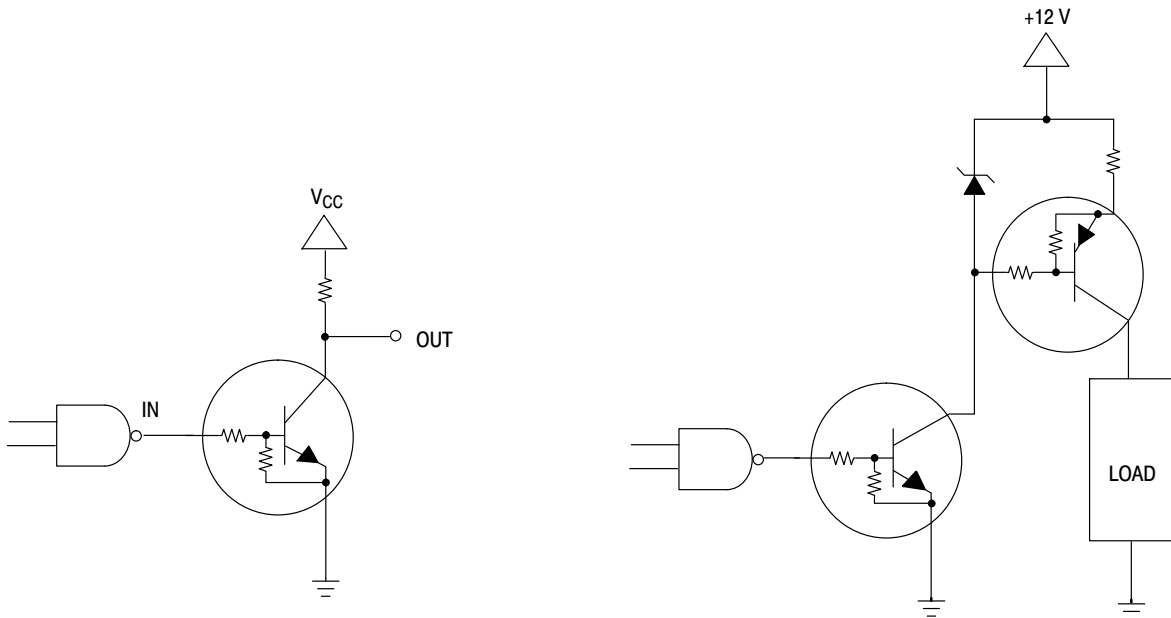


Figure 13. Open Collector Inverter:  
Inverts the Input Signal

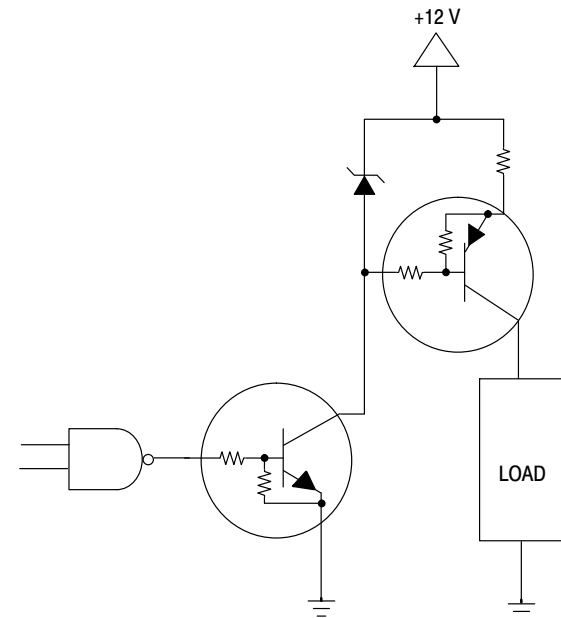


Figure 14. Inexpensive, Unregulated Current Source

## EMG2DXV5, EMG5DXV5

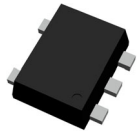
### DEVICE ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
EMG2DXV5T1G	SOT-553 (Pb-Free)	4000 / Tape & Reel
EMG2DXV5T5G	SOT-553 (Pb-Free)	8000 / Tape & Reel
EMG5DXV5T1G	SOT-553 (Pb-Free)	4000 / Tape & Reel
EMG5DXV5T5G	SOT-553 (Pb-Free)	8000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

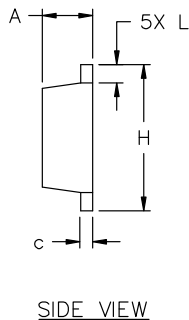
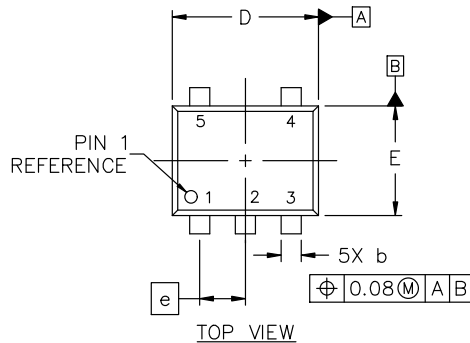


### SOT-553-5 1.60x1.20x0.55, 0.50P

#### CASE 463B

#### ISSUE D

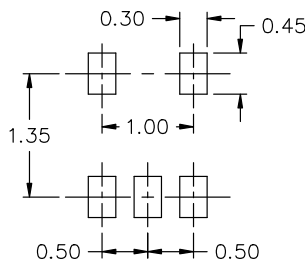
DATE 21 FEB 2024



#### NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
2. ALL DIMENSION ARE IN MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.50	0.55	0.60
b	0.17	0.22	0.27
c	0.08	0.13	0.18
D	1.55	1.60	1.65
E	1.15	1.20	1.25
e	0.50 BSC		
H	1.55	1.60	1.65
L	0.10	0.20	0.30



#### RECOMMENDED MOUNTING FOOTPRINT\*

- \* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERM/D.

#### GENERIC MARKING DIAGRAM\*



XX = Specific Device Code  
M = Date Code  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:  
PIN 1. BASE  
2. EMITTER  
3. BASE  
4. COLLECTOR  
5. COLLECTOR

STYLE 2:  
PIN 1. CATHODE  
2. COMMON ANODE  
3. CATHODE 2  
4. CATHODE 3  
5. CATHODE 4

STYLE 3:  
PIN 1. ANODE 1  
2. N/C  
3. ANODE 2  
4. CATHODE 2  
5. CATHODE 1

STYLE 4:  
PIN 1. SOURCE 1  
2. DRAIN 1/2  
3. SOURCE 1  
4. GATE 1  
5. GATE 2

STYLE 5:  
PIN 1. ANODE  
2. EMITTER  
3. BASE  
4. COLLECTOR  
5. CATHODE

STYLE 6:  
PIN 1. EMITTER 2  
2. BASE 2  
3. EMITTER 1  
4. COLLECTOR 1  
5. COLLECTOR 2/BASE 1

STYLE 7:  
PIN 1. BASE  
2. EMITTER  
3. BASE  
4. COLLECTOR  
5. COLLECTOR

STYLE 8:  
PIN 1. CATHODE  
2. COLLECTOR  
3. N/C  
4. BASE  
5. EMITTER

STYLE 9:  
PIN 1. ANODE  
2. CATHODE  
3. ANODE  
4. ANODE  
5. ANODE

DOCUMENT NUMBER:	98AON11127D	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	SOT-553-5 1.60x1.20x0.55, 0.50P	PAGE 1 OF 1

onsemi and onsemi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

**onsemi**, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## ADDITIONAL INFORMATION

### TECHNICAL PUBLICATIONS:

Technical Library: [www.onsemi.com/design/resources/technical-documentation](http://www.onsemi.com/design/resources/technical-documentation)  
onsemi Website: [www.onsemi.com](http://www.onsemi.com)

### ONLINE SUPPORT: [www.onsemi.com/support](http://www.onsemi.com/support)

For additional information, please contact your local Sales Representative at  
[www.onsemi.com/support/sales](http://www.onsemi.com/support/sales)